A 16 × 16 CMOS Amperometric Microelectrode Array for Simultaneous Electrochemical Measurements

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Abstract — There is a requirement for an electrochemical sensor technology capable of making multivariate measurements in environmental, healthcare, and manufacturing applications. Here, we present a new device that is highly parallelized with an excellent bandwidth. For the first time, electrochemical cross-talk for a chip-based sensor is defined and characterized. The new CMOS electrochemical sensor chip is capable of simultaneously taking multiple, independent electroanalytical measurements. The chip is structured as an electrochemical cell microarray, comprised of a microelectrode array connected to embedded self-contained potentiostats. Speed and sensitivity are essential in dynamic variable electrochemical systems. Owing to the parallel function of the system, rapid data collection is possible while maintaining an appropriately low-scan rate. By performing multiple, simultaneous cyclic voltammetry scans in each of the electrochemical cells on the chip surface, we are able to show (with a cell-to-cell pitch of 456 µm) that the signal cross-talk is only 12% between nearest neighbors in a ferrocene rich solution. The system opens up the possibility to use multiple independently controlled electrochemical sensors on a single chip for applications in DNA sensing, medical diagnostics, environmental sensing, the food industry, neuronal sensing, and drug discovery.

Index Terms — Amperometric sensors, CMOS, cyclic voltammetry, electrochemical sensor, electrochemical cross-talk, microelectrodes, potentiostat.

I. INTRODUCTION

THE electrochemical cell, first demonstrated by Volta and Banks [1], is the foundation of many chemical, biological and sensing technologies [2]. Applications include the popular point-of-care glucose sensor [3], commercial electrochemical gas sensors [4], epiretinal implants [5] and the study of electrogenic cells to further understand the most complex human organ, the brain [6]. In recent years, the microelectrode array (MEA) has risen to prominence in biomedical and environmental redox sensing owing to the low-cost possibility of making many measurements in parallel with high current densities in small volumes, and detection of electroactive species at low concentrations [7]. Despite many advances in the technology [8], numerous problems have yet to be overcome, including low data acquisition speed and poor isolation between electrochemical cells. The latter leads to high cross-talk between adjacent sensors and an inability to make many independent measurements in parallel. We describe and implement a novel complementary metal oxide semiconductor (CMOS) scalable architecture combining new electrode layouts and circuits that enable a reliable planar system of electrodes, connected to an array of potentiostats. Integrating the electrode system in CMOS offers improved signal-to-noise ratio (SNR), parallel data collection, a high-level of circuit and microelectrode integration and fast adaptable spatiotemporal multiplexing at a low unit cost [9], [10].

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electrode (WE, CE and RE respectively). A redox reaction is developed by the application of an electric potential between the WE and CE in the electrolyte and the resulting current is measured on the WE. The potential is adjusted so that $V_{\text{controlled}} = V_{\text{WE}} - V_{\text{RE}}$ (set by a function generator) and the RE corrects for the Ohmic (iR) drop that occurs in the electrolyte, electrodes and circuit impedances. By controlling the system using a potentiostat, a range of electrochemical measurements, such as cyclic voltammetry, become possible [11]. Furthermore, potentiostats can also be used to control electrodes in an MEA, as shown in Fig. 1(b). By doing so, electrodes can be miniaturized thus enabling multiple measurements to be made on a single chip. In this work, we present an electrochemical cell microarray (ECM) system that demonstrates a $4 \times 4$ array of wholly independent electrochemical cells each driven by their own potentiostat, as shown in Fig. 1(c). To realize the ECM, a new electrode layout and circuit design was developed.

Electrode layouts are typically designed by evaluating their potential and current density distributions using electrochemical simulations. In previous studies, using MEAs for electrochemical applications, the use of guard rings has been explored to improve the isolation between independently controlled electrodes [5], [12], [13]. Improved isolation was shown experimentally and by simulation. Planar diffusion of the analyte species led to a “shielding” effect that degraded the electroanalytical performance, as a consequence of overlapping Nernst radial diffusion layers. A 40% decrease of the expected current of a central WE surrounded by other active WEs has been reported [14]. This is regarded as chemical cross-talk [15]. It has been shown that the formation of a planar diffusion layer can be prevented by fabricating the CE in a guard ring structure surrounding the WE [16]. The electrical cross-talk in MEAs occurs because of electrical coupling through the solution or the integrated electronic elements, it has been shown to vary from below 0.1% to more than 10% [17]. Electrical cross-talk has also been observed at neighboring microelectrodes operated at different potentials [18]. There remains a requirement to create arrays capable of multiple concurrent electrochemical experiments that is not possible using the structures outlined above. The main challenge is to minimize both chemical and electrical cross-talk between adjacent electrochemical cells – a problem that has been noted but not addressed to date [19], [20]. Experimental and simulation studies of a new coaxial three-electrode geometry and a unified electrochemical cross-talk figure of merit are presented.

In order to verify our new electrode system, we designed and implemented an integrated circuit. Although cross-talk has not previously been quantified, fast scan cyclic voltammetry (FSCV) along with other electrochemical techniques have been explored using separate, non-integrated, microfabricated electrodes [20], [21]. Previous work on CMOS has shown that electrodes can be set at various offset voltages by a single integrated potentiostat [22]. In an attempt to overcome the current supply limitation of using a single potentiostat it was shown that several potentiostats could be integrated and used simultaneously to perform a single measurement [23]. In this paper, a CMOS ECM is presented, comprised of fully differential potentiostats [24], capable of regulating intercell potential interference. Our device is capable of performing independent concurrent analyte-tailored analysis by different types of electroanalytical techniques on every cell simultaneously, including constant potential amperometry and square wave voltammetry. The high bandwidth potentiostats allow for FSCV to be used at high scan rates and different potential settings can be applied per electrochemical cell. Au bio-functionalizable electrodes were integrated to enable multiplexed DNA “probe” monolayer synthesis [25]. These features allow for the development of an electrochemical DNA microarray [23], [26] for genotyping with increased selectivity. The microarray would allow identifying a hybridized DNA “target” sequence per cell which would be tagged with redox labels, such as ferrocene and its derivatives, each with a different redox potential [27].

The way in which the system was designed to enable independent measurements, allowed for another feature to be exploited. By the use of a novel technique that allows independent control over each cell in an array, we obtained undistorted cyclic voltammograms (CVs) faster than their low scan rates ($\nu$) would normally allow. This feature can be used for other applications that involve short-lived intermediate compounds.

This paper is organized as follows. Section II describes the electrochemical modeling and simulations that lead to an independent electrode configuration. Section III focuses on the electronic circuit design of the array and Section IV details the post-processing steps on the CMOS die. In Section V the chip is characterized and in Section VI details methods and experimental results that demonstrate the electrochemical cells’ independence of operation are presented. In Section VII our system is compared to the state-of-the-art and in Section VIII the paper is concluded.

### II. ELECTROCHEMICAL CELL MICROELECTRODE LAYOUT SIMULATIONS

In order to develop a complete circuit simulation, it was necessary to develop an electronic model for the behavior of the analyte and its interaction with the electrode layout using simulation methods fully compatible with integrated circuit computer-aided design (CAD) software (Cadence®). A suitable layout for the electrodes was investigated for an electrochemical cell array, with cells operating independently of each other. Fig. 2(a) shows a conventional pattern of electrodes, similar to the ones used in previous work [23] and Fig. 2(b) shows a coaxial structure we designed with the CE and RE surrounding the WEs. For the purposes of this simulation we used 4 WEs as a representative example. To understand the electric field and potential distribution associated with the patterns in a chemical solution we developed an equivalent circuit model using a netlist comprising of resistors and capacitors [28]. The electrical model for an electrolyte in solvent was constructed by a 3D cubic mesh of resistors, $R_{\text{eq}}$ as in [29] for a solution volume of 200 $\mu$m $\times$ 200 $\mu$m $\times$ 90 $\mu$m. In our simulation we assumed the solution to be made up of 0.1 M tetrabutylammonium hexafluorophosphate (TBAPF$_6$) in
acetonitrile with a resistivity $\rho = 60.82 \text{ \Omega \cdot cm}$ [30]. From this $R_\text{el} = \rho/\lambda$ could be determined, where $\lambda$ is the grid size of the cubic lattice; $x$ in our simulations was chosen to be 10 $\mu\text{m}$, hence $R_\text{el} = 60.82 \, \text{k}\Omega$. The WE, CE and RE were modelled in a transmission line format [31] in order to take into account their geometries. They were modelled as two dimensional elements of a 10 $\mu\text{m} \times 10$ $\mu\text{m}$ area and represented as points in Fig. 2(a) and 2(b); WE elements were modelled as a 20 $\mu\text{m} \times 20$ $\mu\text{m}$ area. These points were connected together with 40 $\text{m}\Omega/\square$ resistors, which was the sheet resistance of a typical metal layer in a CMOS process, to form the shapes of electrodes. Each point was connected to the mesh using a Randles electrode-electrolyte model [32], [33] as shown in Fig. 2(c).

To determine the component values of the Randles model the addition of 20 mM of ferrocene ($\text{Fe}($C$_5H_5$)$_2$) to the solvent was assumed. $R_\text{CT}$ is the charge transfer resistance calculated from a low field approximation of the Butler-Volmer equation for well stirred solutions [33]:

$$i = i_0 \frac{zF\eta}{U_1}$$

(1)

where $i_0$ is the equilibrium exchange current, $z$ is the number of exchanged electrons, $\eta$ is the overpotential and $U_1 = RT/F$ is the thermal potential, where $R$ is the gas constant, $T$ is the temperature and $F$ is Faraday’s constant. For low fields, (1) can be translated into Ohms law $R_\text{CT} = U_1/i_0z$. $i_0$ was calculated by the equation $i_0 = AFk^0C_\text{R}^\alpha C_\text{O}^{1-\alpha}$ [34], where $A$ is the electrode area, $C_\text{R}$ and $C_\text{O}$ are concentrations of the reduced and oxidized form of the analyte respectively, $\alpha$ is the transfer coefficient and $k^0$ is the standard rate constant. $k^0$ was calculated by experimental observations [35], using a CHI600D commercial potentiostat from CH Instruments. $R_\text{W}$ and $C_\text{W}$ is the Warburg impedance for non-Faradaic processes. An important parameter for its calculation is ferrocene’s diffusion coefficient, $D_\text{FC}$ [36]. $C_1$ is the combination of Helmholtz and Gouy-Chapman capacitance describing the electrical double layer calculated by the Stern-Gouy-Chapman model [36]. Parameters required to calculate $C_1$ include the dielectric constant ($\epsilon_r$) of acetonitrile, and the electrical double layer thickness ($d_\text{OHP}$) [33], [37].

### Table: Parameters Required for the Calculation of Randles Model Impedances

<table>
<thead>
<tr>
<th>Parameter used for calculations</th>
<th>Values</th>
<th>Calculated Randles impedance values specific to the solution composition assumption and the model impedances values are all summarized in Table I.</th>
</tr>
</thead>
<tbody>
<tr>
<td>$\rho$</td>
<td>60.82 $\Omega \cdot \text{cm}$ [30]</td>
<td>$R_{\text{CT}}$</td>
</tr>
<tr>
<td>$z$</td>
<td>1</td>
<td>$R_\text{W}$</td>
</tr>
<tr>
<td>$U_1$</td>
<td>26 mV @ 298K [33]</td>
<td>$C_\text{W}$</td>
</tr>
<tr>
<td>$k^0$ [35]</td>
<td>6.74 m/s</td>
<td>$C_1$</td>
</tr>
<tr>
<td>$\alpha$ [35]</td>
<td>0.6</td>
<td>$R_5$</td>
</tr>
<tr>
<td>$d_\text{OHP}$ [33], [37]</td>
<td>0.314 $\mu\text{m}$</td>
<td>$D_\text{FC}$</td>
</tr>
</tbody>
</table>

Impedance values were calculated for a 10 $\mu\text{m} \times 10$ $\mu\text{m}$ electrode area.

Having developed netlists representing electrode layouts in a chemical solution, we used them in an integrated circuit simulation (Cadence®) of a fully differential potentiostat design [24]. A dc response was recorded as a snapshot. The potential distribution in each cell was plotted against its $V_{\text{WE}}$, since $V_{\text{controlled}} = -(V_{\text{RE}} - V_{\text{WE}})$. Owing to the differential nature of the potentiostats $V_{\text{WE}}$ was adjusted at a different level for each electrochemical cell. The simulation ignored effects of mass transfer and electro-osmosis.

The simulation results for the electric field, the potential distribution and the current density are presented in Fig. 3. We used a coaxial geometry to isolate the WE’s inside their respective cells. As it can be observed in Fig. 3 (a) and (b), a close WE pitch is responsible for overlapping electric field intensity areas, which has been identified as a source of electrical cross-talk [13]. The electric field is also associated with analyte diffusion [11], the separation of radial diffusion layers among the WE’s is essential for high mass transfer behavior on microelectrodes [15]. The coaxial geometry was designed to meet those requirements.

Concerning the potential distribution, the simulations showed that a potentiostat would establish a defined potential around the RE. The potential of the CE was adjusted to a higher value than $V_{\text{RE}}$ to compensate for the $iR$ drop, as evident in Fig. 3(c-f). The effect of the electrode layout is prominent in the electric field and current density, which are related by $J = E/\rho$. Whereas for the conventional geometry the current was estimated to flow from the CE to the WE’s in a cylindrical shape, shown in Fig. 3(c) and (e), an inwards cycling “fountain” flow would occur at the coaxial geometry, as shown in Fig. 3(d) and (f). Moreover, the coaxial layout benefits from an equipotential area, which would develop in the vicinity of the RE and be guarded by the surrounding CE, as displayed in Fig. 3(d). Although the use of CE rings around each WE could improve intra-cell isolation, it was not done in order to minimize capacitive coupling caused by interconnections between CE rings.
Fig. 3. A YZ slice of the electric field intensity at the WEs of (a) a conventional and (b) a coaxial geometry. 3D Potential distribution against $V_{WE}$ and current density vector of (c) a conventional and (d) a coaxial geometry. (e) Slices of potential distribution and current density vector for simultaneously operated adjacent electrochemical cells in a conventional and (f) a coaxial geometry against every cell’s $V_{WE}$. The cells were set at $V_{controlled\_cell1} = -1.5$ V & $V_{controlled\_cell2} = -0.5$ V respectively.

Cells were simulated in pairs of 4 WEs set at different potential levels. The simple design of the conventional pattern resulted in poor regulation of the potential distribution, as observed on the left cell of Fig. 3(e). The source of the problem was an inter-cell leakage current originating from the CE of the neighboring cell. Conversely a lower leakage current, mainly between CEs, was observed in simulations among coaxially patterned cells, as shown in Fig. 3(f). The coaxial arrangement regulated the CE potential accordingly to maintain a stable intra-cell current flow to the WEs and limit inter-cell mass transfer.

By simulating the behavior of the entire system, including electronics and electrode kinetics, we gained a unique insight into the operation of the device. The coaxial electrode pattern exhibited promising results for its use in an ECM, especially when combined with a fully differential potentiostat in a design explained in the next section.

III. INDEPENDENT ELECTROCHEMICAL CELL MICROELECTRODE ARRAY CMOS DESIGN

The ECM design consists of $4 \times 4$ electrochemical cells arranged in a 456 $\mu$m pitch. Electrodes were integrated together with electronics on the same CMOS chip to enable localized control. Each cell contains a 16 WE sub-array and a fully differential potentiostat [24] driven by separate differential input signals. The sub-array WEs were arranged in a 114 $\mu$m pitch coaxial geometry surrounded by a CE and a RE. The geometry was based on our layout simulations and it was expected to follow the behavior of the simulated 4 WE geometry (Fig. 4(a)).

The integrated potentiostat is comprised of OP1, a two-stage high gain fully differential folded cascode control opamp with a common mode feedback loop (CMFB) [38] and 2 unity gain amplifiers (OP2 and OP3), as shown in Fig. 4(b). The fully differential control opamp, shown in Fig. 5, allows for common mode noise suppression and individual regulation of the CE and WEs potentials. This feature is critical for applying independent multiple voltammetric electrochemical experiments, as well as increasing the output voltage swing of low-voltage CMOS circuits towards a broader analyte selection range.

Using our simulation netlist, the control opamp was designed to have a unity gain bandwidth of 3.3 MHz with a phase margin of 110° since it was Miller compensated, and a DC gain of 77 dB. To achieve these specifications the power dissipation was 940 $\mu$W. A circuit of high sheet resistance integrated polysilicon resistors of 500 k$\Omega$ coupled with 1 pF compensation polysilicon capacitors was used to detect the common mode signal in the CMFB. The compensation and CMFB needed in the opamp are largely responsible for the dissipation figure. Each of the unity gain amplifiers dissipated 234 $\mu$W in simulation, and exhibited a unity gain bandwidth of 29 MHz with a phase margin of 113° and a DC gain of 92 dB.

Overall the system operates as follows. A pair of input voltages, $V_{IN+}(i)$ and $V_{IN-}(i)$, are supplied externally to each potentiostat. These voltages drive the control opamp (OP1) and a feedback loop by the unity gain amplifiers (OP2 and OP3) maintains the potential difference of $V_{WE} - V_{RE}$ in each potentiostat. A redox reaction develops at the WEs which are multiplexed by $WE_{EN}$ using a rolling shutter method. The related current is converted to the output voltage at the cell’s readout resistor $(R_{1\_to\_V})$. The output voltage changes represent the degree of reduction or oxidation occurring at the WE.

Unlike the conventional readout method, where the entire applied potential waveform is required to be scanned through each WE, our WE sub-array was designed so that electrodes were multiplexed over segmented voltage levels. However,
Multiplexing can cause voltage perturbation and as a consequence a disturbance of the analyte diffusion layer. To prevent such problems and sustain the current flow all WEs were connected to similar potentials (within a few mV). Non-addressed WEs were connected to the negative output of the control opamp by the $WE_{EN}$ switches [16], [39], as shown in Fig. 4(b).

A novel additional feature was also added to the design to enable the chip’s functionalization e.g. electrodeposition. Microelectrodes can be functionalized using a voltage potential that can be applied externally ($V_{func\_CEs}$, $V_{func\_REs}$ and $V_{func\_WEs}$), as shown in Fig. 4. The selection of each type of electrodes can be enabled using integrated switches (transmission gates) incorporated in each cell ($CE\_func\_EN$, $RE\_func\_EN$ and $WE\_func\_EN$). To isolate the electrodes during functionalization the driving circuit is disconnected by switches ($S1$ and $S2$). When the ECM was normally operated, all $func\_EN$ control signals were on the “off” position and $V_{func\_pins}$ were connected to ground.

The system was designed in a 4-metal 350-nm CMOS process and was fabricated by ams AG through the Europractice mini@sic multi project wafer service. The array’s active area is $1.814 \text{ mm} \times 1.814 \text{ mm}$.

In order to test and validate the chip, the inputs and outputs were connected to a National Instruments® PXIe interface system, which consisted of a PXIe-1073 chassis and three cards, a PXI-6723, a PXI 6704 for the analogue inputs and a PXIe-6358 with a 1.25 MS/s/channel capability that read the analogue outputs. A LabVIEW program was developed to perform electrochemical experiments and analyze the results. WEs were switched at frequencies up to 6.4 kHz with a sampling rate of 32 kS/s/channel for the analogue outputs.

In order to prepare the microelectrodes on CMOS technology so that experiments could be carried out, it was necessary to perform post-processing. This is described in Section IV.

IV. ECM POST PROCESSING AND ENCAPSULATION

The electrodes were coated with Au since it makes them more electrochemically inert. Furthermore, Au can be readily modified e.g. with thiol chemistry for use in biosensing applications. The Al metal used by the foundry is not biocompatible and degrades easily. 800 nm of the 1 $\mu$m thick Si$_3$N$_4$ part of the passivation layer over the electrode array area was removed by etching. An overglass opening was made on the remaining passivation layer covering the Al electrodes which were designed on the top metal layer of the CMOS process and are shown in Fig. 6(a) and (c). The opening was patterned at a width 25 % smaller than the 20 $\mu$m side of the square WEs and the 11 $\mu$m wide REs and CEs using a positive photoresist (Microposit™ S1818™) and etched via a reactive ion etch process of CHF$_3$/O$_2$. A pattern wider than the Al electrodes was then photolithographically defined to cover the easily corroded Al metal with a chemically resistant layer. The photoresist was pre-soaked in a tetramethylammonium hydroxide (TMAH) based developer to create an inhibition layer and form a suitable overhang [40] for metal liftoff.

A stack of metal layers comprised of 20 nm Ti, 50 nm Pd and 200 nm Au was thermally evaporated and microelectrodes were formed by a liftoff process, as shown in Fig. 6(b) and (d). Pd was used as a diffusion barrier between Al and Au preventing the formation of an Al-Au intermetallic that leads to poor conductivity [41]. The exposed Al CMOS top metal layer formed a thin native Al$_2$O$_3$ layer by coming in contact
with an O₂ rich environment. Tests on dummy samples, shown in Fig. 6(e-f), proved the barrier effect was caused by the oxide layer. This layer was removed by an in-situ Ar etching step before metal evaporation. In addition to the post-processing methods, an added 650 nm layer of Au was electrodeposited with a rate of 65 nm/min using the embedded functionalization method. Optical images of the post-processed chip and a close-up of the electrodes forming a single electrochemical cell are shown in Fig. 7(a).

On completion of post-processing the CMOS chip had to be encapsulated to handle liquids in a container. The die was first bonded on a ceramic PGA-144 chip carrier with an H74 epoxy from Epoxy Technology. A chemically resistive epoxy 302-3M from Epoxy Technology was used to cover and insulate the bonding wires from the solution. In order to keep the sensor array active area exposed, a polydimethylsiloxane (PDMS) cube was used to create a temporary bond and protect the active area from being covered by the epoxy until it was cured [42]. A polyethylene terephthalate glycol-modified (PETG) custom designed 3D printed test tube with a lid was then fitted using the same epoxy. The chemically resistant materials created a chamber for the chemical solutions that were electrochemically analyzed. The post-processed CMOS die in its encapsulated packaging is illustrated in Fig. 7(b).

In order to verify the ability of the platform to control and monitor redox reactions, the device had to be tested with a well-documented reference substrate. As discussed in the introduction ferrocene is an ideal candidate since it is one of the most common redox species used in electrochemical experiments for its easy to observe current peaks and its reversible properties. Ferrocene is oxidized to ferrocenium according to the reaction:

$$\text{Fe(C₅H₅)₂}^{+} \rightarrow \text{Fe(C₅H₅)₂}^{2+} + e^- \quad (2)$$

Its half-wave potential is $E_{1/2} = 415$ mV when using a Ag⁺/AgCl reference electrode in acetonitrile [43]. The sample solutions were prepared using 99% pure acetonitrile (CH₃CN) and ferrocene (Fe(C₅H₅)₂) with 98% purity, both from ACROS Organics™ (purchased from Fischer Scientific). Tetrabutylammonium hexafluorophosphate (TBAPF₆) was used as the supporting electrolyte with 98% purity from Sigma Aldrich.

The on-chip potentiostats were first benchmarked against a commercial CHI600D potentiostat from CH Instruments. To keep the measurements standardized the aforementioned detectable current, bandwidth, slew rate and the on-chip resistor values. The CMOS potentiostat was configured to have a unity gain by using 10 MΩ external discrete component resistors to mimic the impedance between the microelectrodes. The value of the resistors was chosen so that the current was maintained at the expected experimental levels. The amplifiers’ Miller compensation resulted in a measured potentiostat bandwidth of 150 kHz, allowing FSCV at scan rates of up to 18 KV/s for a 4 Vpp potential scan. The potentiostat slew rate plays an important role in the correct representation of a CV and it was measured to be 1.09 V/µs. The maximum detectable current $I_{\text{max}}$ was determined by adjusting a resistor load. Its value was found to be 13 µA using a 5 kΩ load between the RE and WE and a 50 mV input signal. To avoid measurement variations due to the tolerance of the on-chip RItoV resistors (i.e. ± 20 %), the actual value of each resistor was measured for every chip. The measured values were then used as a reference to calculate the current from voltage measurements.

VI. ELECTROCHEMICAL MEASUREMENTS

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The on-chip potentiostats were first benchmarked against a commercial CHI600D potentiostat from CH Instruments. To keep the measurements standardized the aforementioned
Section IV was used with both potentiostats. A Ag+/AgCl external RE that was made by electrolyzing a Ag wire in 3 M KCl and a Pt wire as a CE were used for the purpose of these experiments. Solutions of 1 mM, 3 mM, 5 mM and 10 mM ferrocene in acetonitrile with 0.1 M TBAPF₆ were prepared. Acetone and isopropanol were used to rinse and clean the microelectrodes between experiments. The CVs were run on both devices using the same settings of 2 V/s scan rate, scanned in a positive direction and considering the anodic current as positive, plotted in Fig. 8(a) and 8(b). In this experiment the signals of the ASIC were not multiplexed; only one of the chip’s fully differential potentiostats was used to drive the external microelectrode setup. A smoothing filter was applied digitally after signal acquisition to the data from measurements with the chip. As expected CVs exhibited peak currents around \( E_{1/2} \) (as the half-peak potential is \( E_{p/2} \approx 400 \text{ mV} \)), ranging in magnitude proportionally to the analyte concentration. The fully differential design of the CMOS potentiostat enabled us to reach \( V_{\text{WE}} \) vs Ag+/AgCl potentials from \(-2 \text{ V} \) to 2 V despite its 3.3 V bias voltage. Peaks observed at these extreme voltages result from the oxidation and reduction of the solvent and the supporting electrolyte. The results are almost identical in both potentiostats.

After verification of the electronic components, measurements with the post-processed electrodes of the encapsulated CMOS ECM were performed. Staircase voltammetry was performed, by applying a waveform of segmented voltage levels. A common differential waveform, using the same rate as before of 2 V/s, was applied as an input of all independent cells, resulting in a uniform platform monitoring the same reaction. Each cell’s WEs were multiplexed over voltage levels that had a 10 ms duration, as explained in Section IV. Two digital non-linear 1D median filters were applied to data from the output signals to remove impulse noise, originating from the NI PXIe input source. This measurement resulted in 256 concurrent independent CVs monitoring the ion activity at approximately the same points in time. Results from all electrochemical cells were averaged to minimize interference from single WEs. Concentrations of ferrocene from 100 \( \mu \text{M} \) to 10 mM were analyzed and their respective CVs were captured. The anodic and cathodic peak currents of all cells were averaged to demonstrate the peak current signal per concentration response, as shown in Fig. 9. A linear fit line was drawn that describes this relation. The quiescent power dissipation of the microchip was also measured using this experimental arrangement. Using a 0 V DC signal input on all cells the power dissipation was 42.9 mW, whereas on the highest detectable ferrocene concentration and an input waveform at a high scan rate \( v = 8 \text{ V/s} \) it was 125.4 mW. In addition to the power consumption of the internal circuits there are other parameters that can affect the power dissipation such as the chemical solution composition as well as an inter-cell potential difference between CEs as a trade-off of isolation.

A. Cross-Talk

The key feature of this multichannel microelectrode array is the ability to use isolated electrochemical cells in the same solution and perform independent electrochemical techniques simultaneously on the same chip. To demonstrate this capability two experiments were carried out to evaluate cross-talk. In the first of these, the central cell, indicated by a green box in Fig. 10(a), was activated to perform a 2 V/s staircase CV. As can be seen on Fig. 10(b) there is a current detected on the WEs of the activated cell, but negligible current is observed on any of the other cells. The complementary experiment was also conducted whereby the central cell was not activated, but the potential on the neighboring cells was swept, as shown in Fig. 10(c). Fig. 10(d) shows how there is small current detected on the WEs of the inactive central cell. The solution was of the same composition as before with ferrocene at a concentration of 5 mM. The REs in this case were on-chip, fabricated with an Au interface, as explained in Section IV. Au acted as a quasi-reference electrode and is responsible for a redox potential shift to \( E_{p/2} = 75 \text{ mV} \). Each experiment’s values from 50 cyclic voltammetry cycles were averaged and used for the cell-to-cell electrochemical cross-talk calculation, using (3):

\[
\text{cross-talk} = \frac{\sum_{V_n} \frac{T_{\text{central,ac}}(V_n - V_{\text{peak}})}{T_{\text{central,ac}}(V_n - V_{\text{peak}}/2)} \frac{\left| I_{\text{central,ac}}(V_n - V_{\text{peak}}/2) \right|}{N}}{N}
\]

where \( V_{\text{peak}} \) is the potential corresponding to the current peak, \( V_n \) is the range of voltages around the peak that were included in the measurement, \( N \) is the number of samples, \( T_{\text{central,ac}} \) and \( T_{\text{central,in}} \) are the average of the 50 cycle current measurements of the central cell WEs when the cell is active and inactive.
respectively. The inter-cell electrochemical cross-talk was calculated around the current peaks, where it was observed to maximize, using \( V_N = 100 \text{ mV} \). An average value of 12.3 % was obtained, indicating a low leakage current owing to the use of our electrode and circuit design. This cross-talk value was obtained by excluding data values from \( I_{\text{central,ac}} \) and \( I_{\text{central,in}} \) that were lower than the noise floor. The noise floor was calculated by performing a third measurement with all cells at \( V_{\text{WE}} - V_{\text{RE}} = 0 \text{ V} \) for the same duration as a 50 cycle CV and using \( NF = \text{rms}(I_{\text{cell,noise}}(i)) = 1.04 \text{ nA} \), where \( i \) is the cell number and \( I_{\text{cell,noise}}(i) \) is the average current from the WEs of a cell. In addition to the NF, using the same data, the limit of detection (LOD) of the sensor was calculated using: \( LOD = \mu_{I_{\text{cell,noise}}(i)} \pm 3 \times SD_{I_{\text{cell,noise}}(i)} = 880 \pm 510 \text{ pA} \), where \( \mu \) is the mean value and SD the standard deviation. The thermal noise for the 200 k\( \Omega \) \( R_{\text{10 V}} \) resistors is only 8 % of the LOD. The relatively high NF and LOD values are attributed to the accuracy of the PXI readout system with a minimum detectable voltage at 291 \( \mu \text{V} \). Based on these measurements and the \( I_{\text{max}} \) value, the SNR and DR were calculated as 82.6 dB and 75.4 dB respectively.

### B. Multiplexed Cyclic Voltammetry

Using the capability of independently operated electrochemical sensors, one-pot chemical and biological applications become possible. A demonstration of how the low cross-talk value of our single chamber ECM allows for independent potential scans with a low leakage current is illustrated by a novel electrochemical technique that we introduce. We call this technique multiplexed cyclic voltammetry and it increases the equivalent scan rate \( \nu_{\text{eq}} \) by the use of our ECM features. The input waveform function of a CV was resolved over all the electrochemical cells by splitting it into independent (differential) input signals. Each portion of the waveform function was applied to a corresponding electrochemical cell. On every new cycle the waveform function portions were recycled consecutively. In Fig. 10(e) a WE current map at the beginning of the first cycle (after a pre-concentration cycle) is shown, using the sample solution that was used in the electrochemical cross-talk measurement. The current map demonstrates the redox responses to different concurrent waveform settings. Demultiplexing the averaged cell current outputs resulted in a reconstructed CV, shown in Fig. 10(f), results from cells 2, 3 and 10, 11 were excluded to show a range from \(-1.5 \text{ V} \) to \(1.5 \text{ V} \). The CV’s behavior is similar to the response of a normal CV i.e. Fig. 10(b) and 10(d). The advantage of a multiplexed CV is an increase in the resulting equivalent scan rate, according to \( \nu_{\text{eq}} = \nu_{\text{cell}} \times N_{\text{cells}} \), where \( \nu_{\text{cell}} \) is the scan rate used at each electrochemical cell, and \( N_{\text{cells}} \) is the number of electrochemical cells. The CV of Fig. 10(f) has a \( \nu_{\text{eq}} = 24 \text{ V/s} \) which is 12 times faster than a normal CV with \( \nu_{\text{cell}} = 2 \text{ V/s}. \) Scaling up the array with more cells will lead to scan rates comparable to FSCV which suffers from the need to remove background current and also signal distortion caused by the Ohmic drop [46], [47]. Multiplexed cyclic voltammetry maintains the attractive reliable Faradaic current behavior of low scan rates and at the same time increases the temporal resolution. The increased equivalent...
**TABLE II**

<table>
<thead>
<tr>
<th></th>
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<th></th>
</tr>
</thead>
<tbody>
<tr>
<td>Technology</td>
<td>3-electrode SE(^{a})</td>
<td>3-electrode SE(^{a})</td>
<td>3-electrode SE(^{a})</td>
<td>2-electrode SE(^{b})</td>
<td>3-electrode FD(^{b})</td>
</tr>
<tr>
<td>Power Supply Voltage</td>
<td>2.5 V</td>
<td>5 V</td>
<td>3.3 V</td>
<td>3.3 V</td>
<td>3.3 V</td>
</tr>
<tr>
<td>Die Size</td>
<td>5 × 3 mm(^{2})</td>
<td>6.5 × 3 mm(^{2})</td>
<td>7.5 × 4.8 mm(^{2})</td>
<td>3.8 × 3.1 mm(^{2})</td>
<td>3.79 × 3.79 mm(^{2})</td>
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<tr>
<td>Chip Sensing Area</td>
<td>Not Available</td>
<td>~3 × 3 mm(^{2})</td>
<td>3.2 × 3.2 mm(^{2})</td>
<td>3.15 × 1.9 mm(^{2})</td>
<td>1.81 × 1.81 mm(^{2})</td>
</tr>
<tr>
<td>WE size</td>
<td>70 × 70 μm(^{2}) to 100 μm × 100 μm(^{2})</td>
<td>100 μm × 100 μm(^{2})</td>
<td>100 μm long bumps</td>
<td>20 × 20 μm(^{2})</td>
<td></td>
</tr>
<tr>
<td>WE pitch</td>
<td>Not Available</td>
<td>100 μm</td>
<td>100 μm</td>
<td>200 μm</td>
<td>114 μm</td>
</tr>
<tr>
<td>Number of WE(s)</td>
<td>4 × 4 [16]</td>
<td>24 × 24 (576)</td>
<td>32 × 32 (1024)</td>
<td>16 × 12 (192)</td>
<td>16 × 16 (256)</td>
</tr>
<tr>
<td>WE(s) per readout Channel</td>
<td>1</td>
<td>24</td>
<td>16</td>
<td>1</td>
<td>16</td>
</tr>
<tr>
<td>Number of Potentiostats</td>
<td>4</td>
<td>1 (external)</td>
<td>1 (bipotentiostat)</td>
<td>192 (current conveyor)</td>
<td>16</td>
</tr>
<tr>
<td>Number of independent EC()</td>
<td>1</td>
<td>1</td>
<td>1</td>
<td>1</td>
<td>4 × 24(^{a})</td>
</tr>
<tr>
<td>(I(_{\text{max}}))</td>
<td>150 nA</td>
<td>5 μA</td>
<td>2 μA or 10 μA</td>
<td>350 nA</td>
<td>15 μA</td>
</tr>
<tr>
<td>Limit of Detection (LOD)</td>
<td>550 pA(_{\text{max}})</td>
<td>500 pA</td>
<td>100 pA or 1 nA</td>
<td>24 pA</td>
<td>1.39 nA</td>
</tr>
<tr>
<td>Readout SNR</td>
<td>Noise Floor</td>
<td>Not Available</td>
<td>1 μA / channel</td>
<td>300 nA / channel</td>
<td>13 μA / channel</td>
</tr>
<tr>
<td>Cross-talk</td>
<td>Not Available</td>
<td>Not Available</td>
<td>Not Available</td>
<td>Not Available</td>
<td>12.3 %</td>
</tr>
<tr>
<td>Voltage Swing ((V_{\text{pp}}) vs (V_{\text{pp}}))</td>
<td>1.25 (V_{\text{pp}}) (used)</td>
<td>4 (V_{\text{pp}})</td>
<td>2.8 (V_{\text{pp}})</td>
<td>2 (V_{\text{pp}}) (simulated)</td>
<td>5.2 (V_{\text{pp}})</td>
</tr>
<tr>
<td>Slew Rate</td>
<td>Not Available</td>
<td>Not Available</td>
<td>0.35 V/μs</td>
<td>13 V/μs</td>
<td>1.09 V/μs</td>
</tr>
<tr>
<td>Bandwidth</td>
<td>10 kHz</td>
<td>4 kHz</td>
<td>up to 1 kHz</td>
<td>1 kHz</td>
<td>150 kHz</td>
</tr>
<tr>
<td>Max. Sampling Rate</td>
<td>2.5 kS/channel</td>
<td>Not Available</td>
<td>1.4 MS/channel</td>
<td>1 kS/channel</td>
<td>1.25 MS/channel</td>
</tr>
<tr>
<td>Max. Power dissipation</td>
<td>Not Available</td>
<td>25 ± 5 mW</td>
<td>Not Available</td>
<td>188 µW/channel (36 mW)</td>
<td>125.4 mW</td>
</tr>
</tbody>
</table>

\(^{a}\) SE stands for single-ended potentiostat and FD stands for fully differential potentiostat. \(^{b}\) A WE potential setting per 24 current conveyors.
talk of only 12.3% was recorded. As a consequence the electrochemical cells were used independently to perform a new technique that measures a CV more quickly using parallelization. Furthermore, the chip enables a range of different experiments to be carried out simultaneously. These include chronocoulometry and differential pulse voltammetry. The demonstrated electrode system can be scaled up to larger arrays with more electrochemical cells. As the measurements indicate, the ECM is suitable for use as a DNA microarray with several redox labels analyzed with FSCV using electrochemical cells operating in different potential windows. In conventional systems the diffusion of redox labels and cross-hybridization of DNA “targets” to neighboring electrodes is a source of chemical cross-talk [23], [26], [49]. Our system minimizes the diffusion and improves the selectivity by limiting the detection of each analyte to its respective cell. A future chip could integrate a greater number of electrochemical cells on CMOS and provide the architecture for a sensor system-on-chip complete with a microprocessor, data acquisition, and wireless technology. Such integration could lead to a portable self-contained lab-on-a-chip for environmental and biomedical simultaneous multiple analyte sensing applications.

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